2SB1109, 2SB1110

Silicon PNP Epitaxial

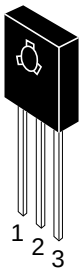
HITACHI

Application

Low frequency high voltage amplifier complementary pair with 2SD1609 and 2SD1610

Outline

TO-126 MOD



1. Emitter
2. Collector
3. Base

Absolute Maximum Ratings (Ta = 25°C)

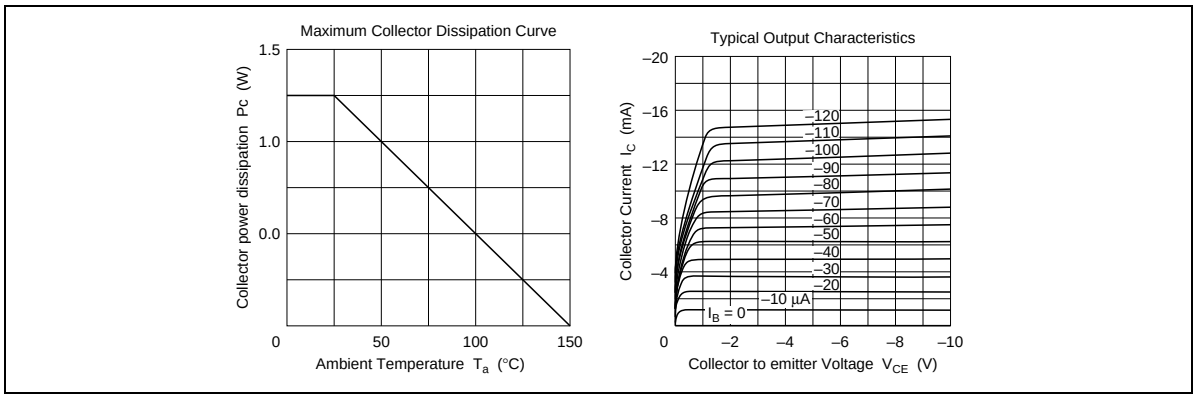
		Ratings		
Item	**Symbol**	**2SB1109**	**2SB1110**	**Unit**
Collector to base voltage	V_{CBO}	–160	–200	V
Collector to emitter voltage	V_{CEO}	–160	–200	V
Emitter to base voltage	V_{EBO}	–5	–5	V
Collector current	I_C	–100	–100	mA
Collector power dissipation	P_C	1.25	1.25	W
Junction temperature	Tj	150	150	°C
Storage temperature	Tstg	–45 to +150	–45 to +150	°C

Electrical Characteristics (Ta = 25°C)

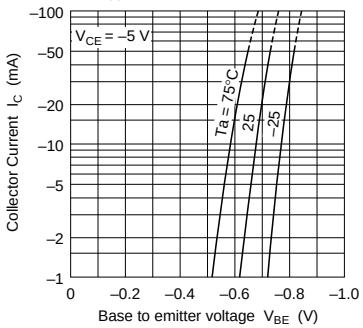
Item	Symbol	2SB1109 Min	2SB1109 Typ	2SB1109 Max	2SB1110 Min	2SB1110 Typ	2SB1110 Max	Unit	Test conditions
Collector to base breakdown voltage	$V_{(BR)CBO}$	–160	—	—	–200	—	—	V	I_C = –10 µA, I_E = 0
Collector to emitter breakdown voltage	$V_{(BR)CEO}$	–160	—	—	–200	—	—	V	I_C = –1 mA, R_{BE} = ∞
Emitter to base breakdown voltage	$V_{(BR)EBO}$	–5	—	—	–5	—	—	V	I_E = –10 µA, I_C = 0
Collector cutoff current	I_{CBO}	—	—	–10	—	—	—	µA	V_{CB} = –140 V, I_E = 0
		—	—	—	—	—	–10	µA	V_{CE} = –160 V, I_E = 0
DC current tarnsfer ratio	h_{FE1}*[1]	60	—	320	60	—	320		V_{CE} = –5 V, I_C = –10 mA
	h_{FE2}	30	—	—	30	—	—		V_{CE} = –5 V, I_C = –1 mA
Base to emitter voltage	V_{BE}	—	—	–1.5	—	—	–1.5	V	I_C = –5 V, I_C = –10 mA
Collector to emitter saturation voltage	$V_{CE(sat)}$	—	—	–2	—	—	–2	V	I_C = –30 mA, I_B = –3 mA
Gain bandwidth product	f_T	—	140	—	—	140	—	MHz	V_{CE} = –5 V, I_C = –10 mA
Collector output capacitance	Cob	—	5.5	—	—	5.5	—	pF	V_{CB} = –10 V, I_E = 0, f = 1 MHz

Note: 1. The 2SB1109 and 2SB1110 are grouped by h_{FE1} as follows.

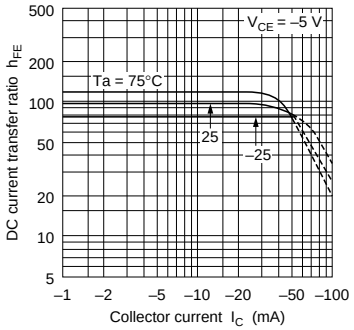
B	C	D
60 to 120	100 to 200	160 to 320



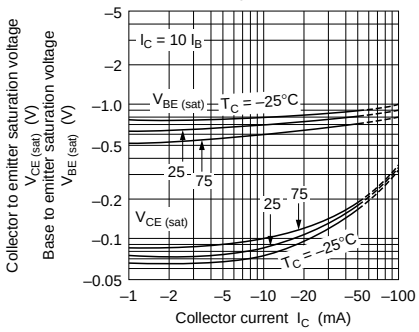
Typical Transfer Characteristics



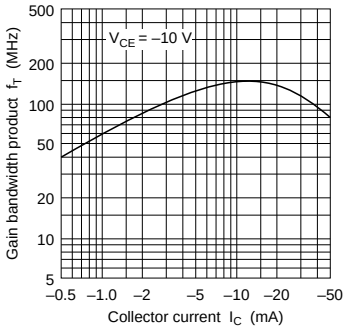
DC Current Transfer Ratio vs. Collector Current



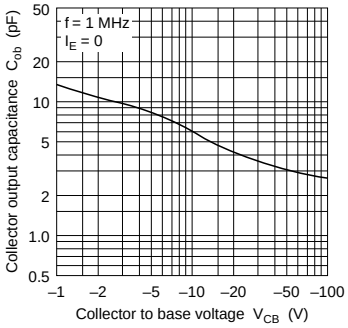
Saturation Voltage vs. Collector Current



Gain Gandwidth Product vs. Collector Current



Collector Output Capacitance vs. Collector to Base Voltage



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